

REMARKS

Claims 1-12, 16, 29, 30 and 32 have been rejected under 35 USC 103(a) as being unpatentable over U.S. patent no. 6,063,677 ("Rodder") in view of U.S. patent no. 5,937,300 ("Sekine") and U.S. patent no. 6,051,473 ("Ishida"). Claims 13-15 and 31 have been rejected under 35 USC 103(a) as being unpatentable over Rodder, Sekine, and Ishida, and further in view of U.S. patent 6,054,355 ("Inumiya"). Claims 17-19 have been rejected under 35 USC 103(a) as being unpatentable over Rodder, Sekine, Ishida, and Inumiya and further in view of U.S. patent 6,051,865 ("Gardner"). Claim 28 has been rejected under 35 USC 103(a) as being unpatentable over Rodder, Sekine, and Ishida, and further in view of Wolf. Applicants respectfully traverse these rejections in view of the amendment because the cited references do not disclose or suggest every element of any claim, as the following analysis shows.

Claim 1 recites depositing the metal layer directly on the alignment component and the region of the substrate adjacent to the alignment component, wherein previous to said depositing the region of the substrate adjacent to the alignment component has not been doped differently than the region of the substrate covered by the alignment component. Support for this limitation may be found in the specification in Figs. 2a, 2b and the descriptive text on page 9 lines 3-19. The applicable references cited in the Office Action all selectively dope the source/drain regions of the substrate differently than the portion of the substrate under the gate and/or alignment component, before applying a metal layer.

The remaining claims all depend, either directly or indirectly, from claim 1 and therefore contain the same limitations not disclosed or suggested by the cited references.

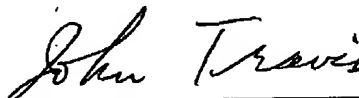
CONCLUSION

For the foregoing reasons, Applicant submits that claims 1-19 and 28-32 are now in condition for allowance, and indication of allowance by the Examiner is respectfully requested. If the Examiner has any questions concerning this application, he or she is requested to telephone the undersigned at the telephone number shown below as soon as possible. No fee is believed due in connection with this amendment. In this is incorrect, please charge any insufficiency or credit any overpayment to Deposit Account No. 02-2666.

Respectfully submitted,

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APPENDIX A**MARKED UP VERSION OF AMENDED CLAIMS:**

1. (Amended four times) A method of forming a transistor, comprising:

forming an alignment component on a substrate of a semiconductor material, said alignment component consisting of a single material;

depositing a metal layer [over the substrate and] directly on the alignment component and directly on a region of the substrate adjacent to the alignment component, wherein previous to said depositing the region of the substrate adjacent to the alignment component has not been doped differently than a region of the substrate covered by the alignment component;

reacting the metal layer with the semiconductor material of the substrate to form two silicide regions, the silicide regions having inner surfaces which face one another, wherein an upper portion of each inner surface contacts the alignment component and a lower portion of each inner surface contacts the semiconductor material of the substrate;

removing the alignment component; and

replacing the removed alignment component with a conductive gate.